

# Quad 2-input NAND gate

## BU4011B / BU4011BF / BU4011BFV

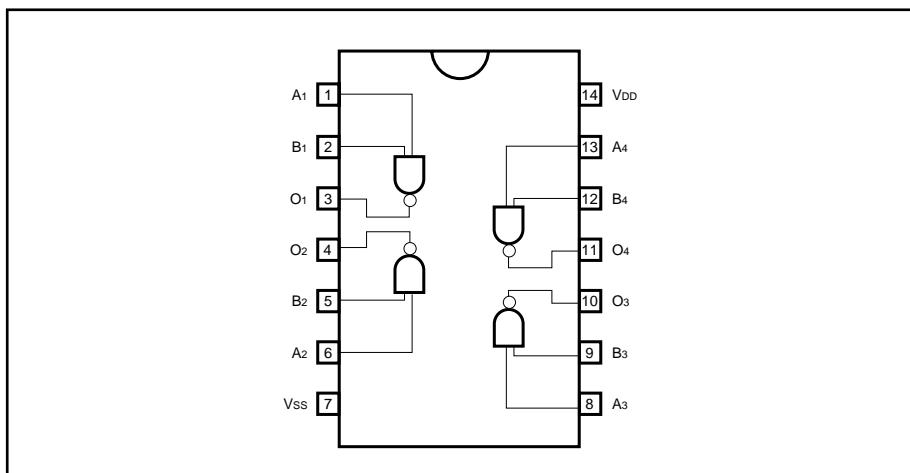
The BU4011B, BU4011BF, and BU4011BFV are dual-input positive logic NAND gates.

Four circuits are contained on a single chip. An inverter-based buffer has been added to the gate output, enabling improved input / output propagation characteristics, and an increased load capacitance minimizes fluctuation in propagation time.

### ●Features

- 1) Low power dissipation.
- 2) Wide range of operating power supply voltage.
- 3) High input impedance.
- 4) High fan-out.
- 5) Direct drive of 2 L-TTL inputs and 1 LS-TTL input.

### ●Block diagram



### ●Absolute maximum ratings ( $V_{ss} = 0V$ , $T_a = 25^{\circ}\text{C}$ )

Parameter	Symbol	Limits	Unit
Power supply voltage	$V_{DD}$	-0.3 ~ +18	V
Power dissipation	$P_d$	1000 (DIP), 450 (SOP) 350 (SSOP-B14)	mW
Operating temperature	$T_{opr}$	-40 ~ +85	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C
Input voltage	$V_{IN}$	-0.3 ~ $V_{DD} + 0.3$	V

## ● Electrical characteristics

DC characteristics (unless otherwise noted,  $V_{SS} = 0V$ ,  $T_a = 25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	$V_{DD}$ (V)	Conditions	Measurement circuit
Input high-level voltage	$V_{IH}$	3.5	—	—	V	5	—	Fig. 1
		7.0	—	—		10		
		11.0	—	—		15		
Input low-level voltage	$V_{IL}$	—	—	1.5	V	5	—	Fig. 1
		—	—	3.0		10		
		—	—	4.0		15		
Input high-level current	$I_{IH}$	—	—	0.3	$\mu A$	15	$V_{IH} = 15V$	Fig. 1
Input low-level current	$I_{IL}$	—	—	-0.3	$\mu A$	15	$V_{IL} = 0V$	Fig. 1
Output high-level voltage	$V_{OH}$	4.95	—	—	V	5	$I_o = 0mA$	Fig. 1
		9.95	—	—		10		
		14.95	—	—		15		
Output low-level voltage	$V_{OL}$	—	—	0.05	V	5	$I_o = 0mA$	Fig. 1
		—	—	0.05		10		
		—	—	0.05		15		
Output high-level current	$I_{OH}$	-0.16	—	—	mA	5	$V_{OH} = 4.6V$	Fig. 1
		-0.4	—	—		10	$V_{OH} = 9.5V$	
		-1.2	—	—		15	$V_{OH} = 13.5V$	
Output low-level current	$I_{OL}$	0.44	—	—	mA	5	$V_{OL} = 0.4V$	Fig. 1
		1.1	—	—		10	$V_{OL} = 0.5V$	
		3.0	—	—		15	$V_{OL} = 1.5V$	
Static current dissipation	$I_{DD}$	—	—	1	$\mu A$	5	$V_I = V_{DD}$ or GND	—
		—	—	2		10		
		—	—	4		15		

Switching characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $V_{ss} = 0\text{V}$ ,  $C_L = 50\text{pF}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit.	$V_{DD}$ (V)	Conditions	Measurement circuit
Output rise time	$t_{TLH}$	—	180	360	ns	5	—	Fig. 2
		—	90	180		10		
		—	65	130		15		
Output fall time	$t_{TFL}$	—	100	200	ns	5	—	Fig. 2
		—	50	100		10		
		—	40	80		15		
“L” to “H” Propagation delay time	$t_{PLH}$	—	90	180	ns	5	—	Fig. 2
		—	50	100		10		
		—	40	80		15		
“H” to “L” Propagation delay time	$t_{PHL}$	—	90	180	ns	5	—	Fig. 2
		—	50	100		10		
		—	40	80		15		
Input capacitance	$C_{IN}$	—	5	—	pF	—	—	—

### ● Measurement circuits

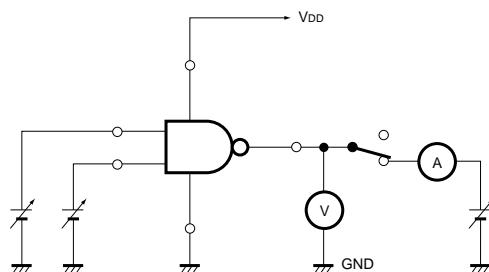


Fig. 1 DC characteristics

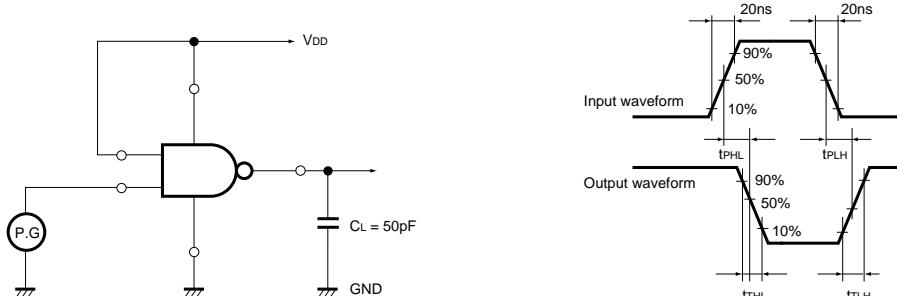


Fig. 2 Switching characteristics

● Electrical characteristic curve

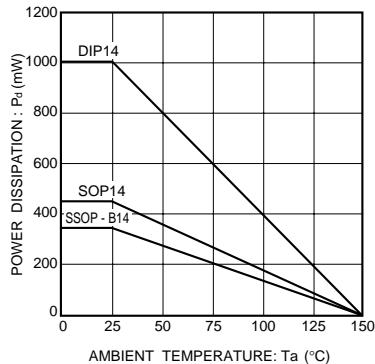


Fig. 3 Power dissipation vs.  $T_a$

● External dimensions (Units: mm)

